
Errors calculation in determining the target carrier density for multicrystalline silicon ingots growth

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The article presents a description of methodology and gives the results of the calculation of errors in determining the target concentration of charge carriers. We identified the basic parameters affecting the accuracy of measurements of the electrical resistance at the bar, obtained by using the described in the article downloads for growth ingots.

Keywords: multicrystalline silicon, carrier density, electrical resistivity, error.

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